

2021-25

25 Watts, 24 Volts, Class C Microwave 2000 - 2130 MHz

The 2021-2 Class C our input and c metalizatio supreme ru Solder Seat	RAL DESCRIPTION 25 is a COMMON BASE transistor ca tput power over the band 2000-2130 I putput prematching for full Broadband on and diffused ballasting are used to p taggedness. The transistor uses a fully f led package.	CASE OUTLINE 55AW, STYLE 1	
ABSO	LUTE MAXIMUM RA	TINGS	$\langle \rangle \rangle$
Maximum	Power Dissipation @ 25°C	58 Watts	$\bigcirc \times \checkmark \times$
Maximum	Voltage and Current		
BVces	Collector to Emitter Voltage	40 Volts	\rightarrow
BVebo	Emitter to Base Voltage	3.5 Volts	
Ic	Collector Current	3.0 Amps	
Maximum	Temperatures		\bigcirc
Maximum Storage Te	-	- 65 to + 200°C	\bigcirc

ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
Pout Pin Pg ηc VSWR1	Power Out Power Input Power Gain Efficiency Load Mismatch Tolerance	F = 2000-2100 MHz Vcc = 24 Volts Pout = 25 Watts	25 7.0	50	5.0 3:1	Watts Watts dB %

BVces BVebo Hfe	Collector to Base Breakdown Emitter to Base Breakdown Current Gain	Ic = 10 mA Ie = 5 mA Vce = 5V, Ic=1 A	40 3.5 20	120	Volts Volts
Cob θjc	Output Capacitance* Thermal Resistance	$Tc = 25^{\circ}C$	1	3.0	pF °C/W

* Not measureable due to internal prematch network

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